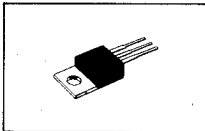




No.1309



**2SC3173**

NPN Epitaxial Planar Type Silicon Transistor  
FOR CRT HORIZONTAL DEFLECTION OUTPUT

**Features:**

- High switching speed
- Especially suited for use in high-definition CRT display ( $V_{CC}=6$  to  $12V$ )
- Wide ASO and durable against breakdown

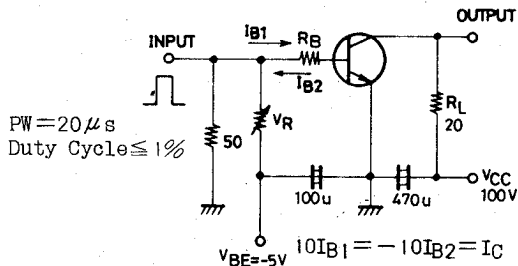
**Absolute Maximum Ratings at  $T_a=25^\circ C$**

			unit
Collector to Base Voltage	$V_{CBO}$	330	V
Collector to Emitter Voltage	$V_{CEO}$	150	V
Emitter to Base Voltage	$V_{EBO}$	6	V
Collector Current	$I_C$	7	A
Peak Collector Current	$i_{cp}$	12	A
Base Current	$I_B$	4	A
Collector Dissipation	$P_C$	$T_c=25^\circ C$	50 W
Junction Temperature	$T_j$	150	$^\circ C$
Storage Temperature	$T_{stg}$	-55 to +150	$^\circ C$

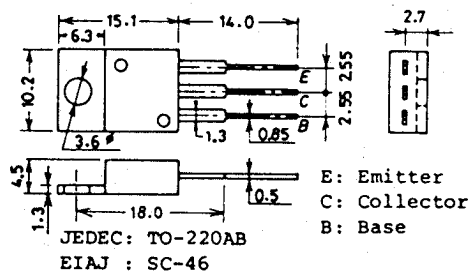
**Electrical Characteristics at  $T_a=25^\circ C$**

			min	typ	max	unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB}=200V, I_E=0$			100	$\mu A$
Emitter Cutoff Current	$I_{EBO}$	$V_{EB}=5V, I_C=0$			100	$\mu A$
DC Current Gain	$h_{FE}(1)$	$V_{CE}=1V, I_C=1A$	15			
	$h_{FE}(2)$	$V_{CE}=1V, I_C=5A$	10		50	
Gain Bandwidth Product	$f_T$	$V_{CE}=10V, I_C=0.5A$	10	40		MHz
C-E Saturation Voltage	$V_{CE}(sat)$	$I_C=5A, I_B=0.5A$			1	V
B-E Saturation Voltage	$V_{BE}(sat)$	$I_C=5A, I_B=0.5A$			1.2	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C=1mA, I_E=0$	330			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C=1mA, R_{BE}=\infty$	150			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E=1mA, I_C=0$	6			V
Fall Time	$t_f$	$I_C=5A, I_{B1}=-I_{B2}=0.5A$			0.5	$\mu s$

**Switching Time Test Circuit**



**Case Outline 2010A (unit:mm)**



Information furnished by SANYO is believed to be accurate and reliable. However, no responsibility is assumed by SANYO for its use; nor for any infringements of patents or other rights of third parties which may result from its use, and no license is granted by implication or otherwise under any patent or patent rights of SANYO.

These specifications are subject to change without notice.